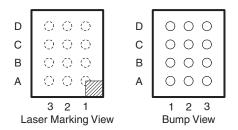
0.7-Ω DUAL SPDT ANALOG SWITCH WITH NEGATIVE RAIL CAPABILITY AND 1.8-V COMPATIBLE INPUT LOGIC

Check for Samples: TS5A22366

FFATURES

- Negative Signaling Capability: Maximum Swing From –2.75 V to 2.75 V (V₊ = 2.75 V)
- Low ON-State Resistance (0.7 Ω Typ)
- Excellent ON-State Resistance Matching
- 1.8-V Compatible Control Input Threshold Independent of V₊
- Control Inputs Are 5.5-V Tolerant
- 2.25-V to 5.5-V Power Supply (V₁)
- · Low Charge Injection
- Specified Break-Before-Make Switching
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II

YFC PACKAGE



- ESD Performance Tested Per JESD 22
 - 2500-V Human-Body Model (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)
 - 200-V Machine Model (A115-A)

APPLICATIONS

- Cell Phones
- PDAs
- Portable Instrumentation
- Audio Routing
- Portable Media Players

YFC PACKAGE TERMINAL ASSIGNMENTS

D	NC1	V ₊	NC2
С	COM1	GND	COM2
В	NO1	GND	NO2
Α	IN1	N.C. ⁽¹⁾	IN2
	1	2	3

(1) N.C. -No internal connection

DESCRIPTION

The TS5A22366 is a dual single-pole double-throw (SPDT) analog switch that is designed to operate from 2.25 V to 5.5 V. The device features negative signal capability that allows signals below ground to pass through the switch without distortion.

The break-before-make feature prevents signal distortion during the transferring of a signal from one path to another. Low ON-state resistance, excellent channel-to-channel ON-state resistance matching, and minimal total harmonic distortion (THD) performance are ideal for audio applications.

The TS5A22366 is available is a ultra small 1.6 mm x 1.2 mm wafer-chip-scale package (WCSP) (0.4 mm pitch).

ORDERING INFORMATION

For package and ordering information, see the Package Option Addendum at the end of this document.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



Table 1. SUMMARY OF CHARACTERISTICS

 $V_{+} = 3.3 \text{ V}, T_{A} = 25^{\circ}\text{C}$

Configuration	2:1 Multiplexer/Demultiplexer (2 × SPDT)
Number of channels	2
ON-state resistance (ron)	0.8 Ω
ON-state resistance match (Δr _{on})	0.08 Ω
ON-state resistance flatness (r _{ON(flat)})	0.3 Ω
Turn-on/turn-off time (t _{ON} /t _{OFF})	199 ns/182 ns
Break-before-make time (t _{BBM})	7.1 ns
Charge injection (Q _C)	120 pC
Bandwidth (BW)	32 MHz
OFF isolation (O _{ISO})	–70 dB at 100 kHz
Crosstalk (X _{TALK})	-70 dB at 100 kHz
Total harmonic distortion (THD)	0.01%
Package option	12-pin WCSP (YFC)

Table 2. FUNCTION TABLE

IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L	ON	OFF
Н	OFF	ON



APPLICATION BLOCK DIAGRAM

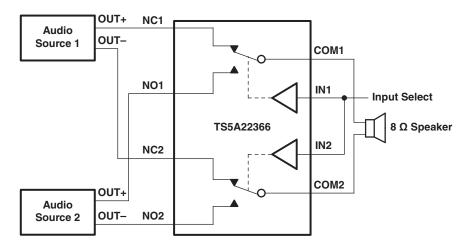


Figure 1. TS5A22366 Application Block Diagram

Negative Signaling Capacity

The TS5A22366 dual SPDT switch features negative signal capability that allows signals below ground to pass through without distortion. These analog switches operate from a single +2.3-V to +5.5-V supply. The input/output signal swing of the device is dependant of the supply voltage V_+ : the devices pass signals as high as V_+ and as low as $V_+ - 5.5$ V, including signals below ground with minimal distortion.

Table 3 shows the input/output signal swing the user can get with different supply voltages.

Table 3. Input/Output Signal Swing

SUPPLY VOLTAGE, V+	$\begin{aligned} & \text{MINIMUM} \\ & (V_{\text{NC}}, V_{\text{NO}}, V_{\text{COM}}) = V_{+} - 5.5 \end{aligned}$	$\begin{array}{c} \text{MAXIMUM} \\ (\text{V}_{\text{NC}}, \text{V}_{\text{NO}}, \text{V}_{\text{COM}}) = \text{V}_{+} \end{array}$
5.5 V	0 V	5.5 V
4.2 V	−1.3 V	4.2 V
3.3 V	−2.2 V	3.3 V
3 V	–2.5 V	3 V
2.5 V	−3 V	2.5 V

Product Folder Links: TS5A22366



ABSOLUTE MINIMUM AND MAXIMUM RATINGS(1) (2)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V ₊	Supply voltage range (3)		-0.5	6	V
$V_{NC} \ V_{NO} \ V_{COM}$	Analog voltage range (3) (4) (5)		V ₊ - 6	V ₊ + 0.5	V
I _K	Analog port diode current ⁽⁶⁾	$V_+ < V_{NC}, V_{NO}, V_{COM} < 0$	-50	50	V
I _{NC}	ON-state switch current	$V_{+} < V_{NC}, V_{NO}, V_{COM} < 0$ $V_{NC}, V_{NO}, V_{COM} = 0 \text{ to } V_{+}$	-150	150	
I _{NO} I _{COM}	ON-state peak switch current ⁽⁷⁾		-300	300	mA
VI	Digital input voltage range		-0.5	6.5	V
I _{IK}	Digital input clamp current (3) (4)	V _{IO} < V _I < 0	-50		mA
I _{GND} I ₊	Continuous current through V₊or GND		-100	100	mA
T _{stg}	Storage temperature range	Storage temperature range			°C

⁽¹⁾ Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

- (2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
- (3) All voltages are with respect to ground, unless otherwise specified.
- (4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (5) This value is limited to 5.5 V maximum.
- (6) Requires clamp diodes on analog port to V₊.
- 7) Pulse at 1-ms duration <10% duty cycle

THERMAL IMPEDANCE RATINGS

				UNIT
θ_{JA}	Package thermal impedance ⁽¹⁾	YFC package	106.2	°C/W

(1) The package thermal impedance is calculated in accordance with JESD 51-7.

ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY⁽¹⁾

 $V_{+} = 2.25 \text{ V}$ to 2.7 V, $T_{\Delta} = -40 ^{\circ}\text{C}$ to 85 $^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONI	DITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM} , V_{NO} , V_{NC}					V ₊ - 5.5		V ₊	Ω
ON-state resistance	r _{on}	V_{NC} or $V_{NO} = V_{+}$, 1.5 V, $V_{+} - 5.5$ V $I_{COM} = -100$ mA,	Switch ON, See Figure 15	25°C Full	2.25 V		1	1.8	Ω
ON-state resistance match between	Δr _{on}	V_{NC} or $V_{NO} = 1.5 \text{ V}$, $I_{COM} = -100 \text{ mA}$,	Switch ON, See Figure 15	25°C Full	2.25 V		0.05	1	Ω
channels ON-state resistance flatness	r _{on(flat)}	V_{NC} or $V_{NO} = V_{+}$, 1.5 V, $V_{+} - 5.5$ V $I_{COM} = -100$ mA,	Switch ON, See Figure 16	25°C Full	2.25 V		0.53	1.5 1.6	Ω
NC, NO OFF leakage current	I _{NC(OFF)} , I _{NO(OFF)}	$\begin{split} &V_{NC} = 2.25, V_+ - 5.5 V \\ &V_{COM} = V_+ - 5.5 V, \\ &2.25, \\ &V_{NO} = Open, \\ ∨ \\ &V_{NO} = 2.25, V_+ - 5.5 V \\ &V_{COM} = V_+ - 5.5 V, \\ &2.25, \end{split}$	Switch OFF, See Figure 16	25°C	2.7 V	-50 -375		375	nA
COM ON leakage current	I _{COM(ON)}	$\begin{split} &V_{NC} = Open, \\ &V_{NC} \text{ and } V_{NO} = Open, \\ &V_{COM} = V_+, V_+ - 5.5 \text{ V}, \end{split}$	See Figure 17	25°C Full	2.7 V	-50 -375		50 375	nA
Digital Control In	puts (IN, EN)	2)				•			
Input logic high	V _{IH}			Full		1.05		5.5	V
Input logic low	V _{IL}			Full				0.65	V
Input leakage current	I _{IH} , I _{IL}	V _{IN} = 1.8 V or GND		25°C Full	2.7 V	-700 -700		700 700	nA

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

Copyright © 2009–2013, Texas Instruments Incorporated

⁽²⁾ All unused digital inputs of the device must be held at V₊ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.



ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY⁽¹⁾ (continued)

 $V_{+} = 2.25 \text{ V}$ to 2.7 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CON	DITIONS	TA	V ₊	MIN	TYP	MAX	UNIT
Dynamic	•				· I				
		V V	C 25 pF	25°C	2.5 V		193	297	
Turn-on time	t _{ON}	$V_{COM} = V_+,$ $R_L = 300 \Omega,$	C _L = 35 pF, See Figure 19	Full	2.25 V to 2.7 V			350	ns
		V V	C 25 pF	25°C	2.5 V			266	
Turn-off time	t _{OFF}	$V_{COM} = V_+,$ $R_L = 300 \Omega,$	C _L = 35 pF, See Figure 19	Full	2.25 V to 2.7 V			320	ns
Break-before- make time	t _{BBM}	$V_{NC} = V_{NO} = V_{+}/2$ $R_{L} = 300 \Omega,$	C _L = 35 pF, See Figure 20	25°C	2.5 V	1	15.6		ns
Charge injection	$Q_{\mathbb{C}}$	$V_{GEN} = 0,$ $R_{GEN} = 0,$	$C_L = 1 \text{ nF},$ See Figure 24	25°C	2.5 V		91		рC
NC, NO OFF capacitance	C _{NC(OFF)} , C _{NO(OFF)}	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch OFF,	See Figure 18	25°C	2.5 V		51		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch OFF,	See Figure 18	25°C	2.5 V		181		pF
COM ON capacitance	C _{COM(ON)}	$V_{COM} = V_{+}$ or GND, Switch ON,	See Figure 18	25°C	2.5 V		181		pF
Digital input capacitance	C _I	$V_I = V_+ \text{ or GND}$	See Figure 18	25°C	2.5 V		3		pF
Bandwidth	BW	$R_L = 50 \Omega$,	Switch ON, See Figure 20	25°C	2.5 V		32		MHz
		$R_1 = 50 \Omega$, Switch	f = 100 kHz,				-70		
OFF isolation	O _{ISO}	OFF,	f = 1 MHz,	25°C	2.5 V		-50		dB
		See Figure 22	f = 5 MHz,				-35		
		P = 50 O Switch ON	f = 100 kHz,				-70		
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, Switch ON, See Figure 23	f = 1 MHz,	25°C	2.5 V		-50		dB
		•	f = 5 MHz,				-35		
Total harmonic distortion	THD	$R_{L} = 600 \Omega,$ $C_{L} = 50 \text{ pF},$	f = 20 Hz to 20 kHz, See Figure 25	25°C	2.5 V		0.02		%
Supply	•								
Positive supply current	I ₊	V _I = 1.8 V or GND,		Full	2.7 V		6	12	μΑ

ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY⁽¹⁾

 $V_{+} = 3 \text{ V to } 3.6 \text{ V}, T_{A} = -40^{\circ}\text{C} \text{ to } 85^{\circ}\text{C} \text{ (unless otherwise noted)}$

PARAMETER	SYMBOL	TEST CON	DITIONS	TA	V ₊	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM} , V_{NO} , V_{NC}					V ₊ - 5.5		V ₊	Ω
		V_{NC} or $V_{NO} \le V_+$, 1.5		25°C			0.8	1.3	
ON-state resistance	r _{on}	$V_{+} - 5.5 V_{+}$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 15	Full	3 V			1.53	Ω
ON-state				25°C			0.08	0.17	
resistance match between channels	Δr_{on}	V_{NC} or $V_{NO} = 1.5 \text{ V}$, $I_{COM} = -100 \text{ mA}$,	Switch ON, See Figure 15	Full	3 V			0.3	Ω
ON-state		V_{NC} or $V_{NO} \le V_+$, 1.5		25°C			0.3	0.65	
resistance flatness	r _{on(flat)}	$V_{+} = 5.5 V_{+}$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 16	Full	3 V	0.75	Ω		
		$V_{NC} = 3, V_{+} - 5.5 V$		25°C		-50		50	
NC, NO OFF leakage current	INC(OFF), INO(OFF)	$\begin{split} &V_{COM} = V_+ - 5.5 \text{ V}, 3, \\ &V_{NO} = \text{Open}, \\ &\text{or} \\ &V_{NO} = 3 \text{ , } V_+ - 5.5 \text{ V} \\ &V_{COM} = V_+ - 5.5 \text{ V}, 3, \\ &V_{NC} = \text{Open}, \end{split}$	Switch OFF, See Figure 16	Full	3.6 V	-375		375	nA
COM		V_{NC} and V_{NO} = Open,	Switch ON	25°C		-50		50	
ON leakage current	I _{COM(ON)}	$V_{COM} = V_+, V_+ - 5.5 V,$		Full	3.6 V	-375		375	nA
Digital Control Inj	outs (IN, EN) ⁽²⁾)		<u></u>				<u> </u>	
Input logic high	V _{IH}			Full		1.05		5.5	V
Input logic low	V _{IL}			Full				0.65	V
Input leakage current	I _{IH} , I _{IL}	V _{IN} = 1.8 V or GND		25°C Full	3.6 V	-920 -920		920 920	nA

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

⁽²⁾ All unused digital inputs of the device must be held at V₊ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.



ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY⁽¹⁾ (continued)

 $V_{+} = 3 \text{ V to } 3.6 \text{ V}, T_{A} = -40 ^{\circ}\text{C} \text{ to } 85 ^{\circ}\text{C} \text{ (unless otherwise noted)}$

PARAMETER	SYMBOL	TEST CO	NDITIONS	TA	V ₊	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t _{on}	$V_{COM} = V_+,$	$C_L = 35 \text{ pF},$	25°C	3.3 V		199	313	ns
	OIV	$R_L = 300 \Omega$	See Figure 19	Full	3 V to 3.6 V			370	
Turn-off time	t _{OFF}	$V_{COM} = V_+,$	$C_L = 35 \text{ pF},$	25°C	3.3 V		182	289.9	ns
	*OFF	$R_L = 300 \Omega$,	See Figure 19	Full	3 V to 3.6 V			350	
Break-before- make time	t _{BBM}	$V_{NC} = V_{NO} = V_{+}/2$ $R_{L} = 300 \Omega,$	$C_L = 35 \text{ pF},$ See Figure 20	25°C	3.3 V	1	7.1		ns
Charge injection	$Q_{\mathbb{C}}$	$V_{GEN} = 0,$ $R_{GEN} = 0,$	$C_L = 1 \text{ nF},$ See Figure 24	25°C	3.3 V		120		рС
NC, NO OFF capacitance	C _{NC(OFF)} , C _{NO(OFF)}	V_{NC} or $V_{NO} = V_{+}$ or $V_{+} - 5.5 V$, Switch OFF,	See Figure 18	25°C	3.3 V		50		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch OFF,	See Figure 18	25°C	3.3 V		180		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 18	25°C	3.3 V		180		pF
Digital input capacitance	C_{l}	$V_I = V_+ \text{ or GND}$	See Figure 18	25°C	3.3 V		3		pF
Bandwidth	BW	$R_L = 50 \Omega$,	Switch ON, See Figure 20	25°C	3.3 V		32		MHz
		$R_L = 50 \Omega$, Switch	f = 100 kHz,				-70		
OFF isolation	O _{ISO}	OFF,	f = 1 MHz,	25°C	3.3 V		-50		dB
		See Figure 22	f = 5 MHz,				-35		
		$R_L = 50 \Omega$, Switch	f = 100 kHz,				-70		
Crosstalk	X _{TALK}	ΟN,	f = 1 MHz,	25°C	3.3 V		-50		dB
		See Figure 23	f = 5 MHz,				-35		
Total harmonic distortion	THD	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, See Figure 25	25°C	3.3 V		0.01		%
Supply					1.				
Positive supply current	I ₊	V _I = 1.8 V or GND		Full	3.6 V		6	13	μΑ

ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY⁽¹⁾

 $V_{+} = 4.5 \text{ V}$ to 5.5 V, $T_{A} = -40 ^{\circ}\text{C}$ to 85 $^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CO	NDITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	$V_{\rm COM}, \ V_{\rm NO}, V_{\rm NC}$					V ₊ - 5.5		V ₊	Ω
ON-state		VNC or VNO = V+,	Switch ON,	25°C			0.7	1	_
resistance	r _{on}	$I_{COM} = -100 \text{ mA},$	See Figure 15	Full	4.5 V			1.36	Ω
ON-state	_	V_{NC} or $V_{NO} = 1.5 \text{ V}$,	Switch ON,	25°C			0.1	0.2	
resistance match between channels	Δr_{on}	$I_{COM} = -100 \text{ mA},$	See Figure 15	Full	4.5 V			0.3	Ω
ON-state		VNC or VNO = V+,	Switch ON,	25°C			0.135	0.37	
resistance flatness	r _{on(flat)}	$I_{COM} = -100 \text{ mA},$	See Figure 16	Full	4.5 V			0.51	Ω
		$V_{NC} = 4.5, V_{+} - 5.5 V$		25°C		–50 50			
NC, NO OFF leakage current	I _{NC(OFF)} , I _{NO(OFF)}	$\begin{split} &V_{\text{COM}} = V_+ - 5.5 \text{ V}, \\ &4.5, \\ &V_{\text{NO}} = \text{Open,} \\ &\text{or} \\ &V_{\text{NO}} = 4.5, V_+ - 5.5 \text{ V} \\ &V_{\text{COM}} = V_+ - 5.5 \text{ V}, \\ &4.5, \\ &V_{\text{NC}} = \text{Open,} \end{split}$	Switch OFF, See Figure 16	Full	5.5 V	-375		375	nA
COM		V_{NC} and V_{NO} = Open,	Switch ON.	25°C		-50		50	
ON leakage current	I _{COM(ON)}	$V_{COM} = V_{+}, V_{+} - 5.5 \text{ V},$	See Figure 17	Full	5.5 V	-375		375	nA
Digital Control Inp	uts (IN, EN) ⁽²⁾								
Input logic high	V _{IH}			Full		1.05		5.5	V
Input logic low	V_{IL}			Full				0.65	V
Input leakage	las la	V _{IN} = 1.8 V or 0		25°C	5.5 V	-1.5		1.5	μA
current	I _{IH} , I _{IL}	VIN - 1.0 V 01 0		Full	3.3 V	-1.5		1.5	μΛ

 ⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
 (2) All unused digital inputs of the device must be held at V₊ or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



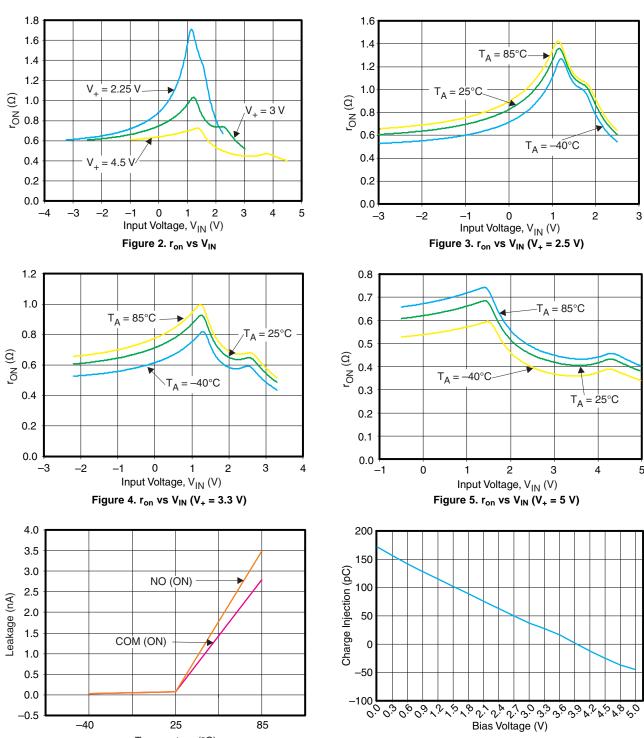
ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY⁽¹⁾ (continued)

 $V_{+} = 4.5 \text{ V}$ to 5.5 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CO	NDITIONS	TA	V ₊	MIN	TYP	MAX	UNIT
Dynamic									
		\/ -\/	$C_{L} = 35 \text{ pF},$	25°C	5 V		230	374	
Turn-on time	t _{ON}	$V_{COM} = V_+,$ $R_L = 300 \Omega,$	See Figure 19	Full	4.5 V to 5.5 V			470	ns
		\/ - \/	C _L = 35 pF,	25°C	5 V		206	325	
Turn-off time	t _{OFF}	$V_{COM} = V_+,$ $R_L = 300 \Omega,$	See Figure 19	Full	4.5 V to 5.5 V			380	ns
Break-before- make time	t _{BBM}	$V_{NC} = V_{NO} = V_{+}/2$ $R_{L} = 300 \Omega$,	C _L = 35 pF, See Figure 20	25°C	3.3 V	1	3		ns
Charge injection	Q _C	V _{GEN} = 0, R _{GEN} = 0,	C _L = 1 nF, See Figure 24	25°C	5 V		168		рС
NC, NO OFF capacitance	C _{NC(OFF)} , C _{NO(OFF)}	V_{NC} or $V_{NO} = V_{+}$ or $V_{+} - 5.5 V$, Switch OFF,	See Figure 18	25°C	5 V		48		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V_{NC} or $V_{NO} = V_{+}$ or $V_{+} - 5.5 V$, Switch ON,	See Figure 18	25°C	5 V		176		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 18	25°C	5 V		176		pF
Digital input capacitance	C _I	$V_I = V_+ \text{ or GND}$	See Figure 18	25°C	5 V		3		pF
Bandwidth	BW	$R_L = 50 \Omega$,	Switch ON, See Figure 20	25°C	5 V		32		MHz
		$R_L = 50 \Omega$, Switch	f = 100 kHz				-70		
OFF isolation	O _{ISO}	OFF,	f = 1 MHz	25°C	5 V		-50		dB
		See Figure 22	f = 5 MHz				-35		<u> </u>
		D 50 O Outub ON	f = 100 kHz				-70		l
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, Switch ON, See Figure 23	f = 1 MHz	25°C	5 V		-5 0		dB
		3	f = 5 MHz				-35		<u></u>
Total harmonic distortion	THD	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, See Figure 25	25°C	5 V		0.01		%
Supply									
Positive supply current	I ₊	V _I = 1.8 V or GND		Full	5.5 V		7	14	μΑ



TYPICAL PERFORMANCE



Temperature (°C) Figure 6. Leakage Current vs Temperature

25

85

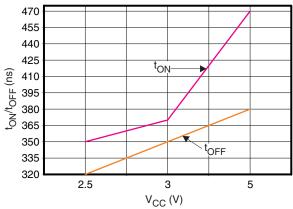
Figure 7. Charge Injection (Q_C) vs $V_{COM}(V_+ = 5 \text{ V})$

-40

-0.5



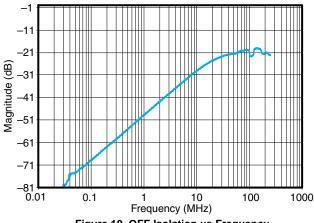




(ap) -4 -5 -5 -6 -6 -7 -7 -7 -10 -11 -12 -13 0.01 0.1 1 10 100 1000 Frequency (MHz)

Figure 8. t_{ON} and t_{OFF} vs Supply Voltage

Figure 9. Bandwidth $(V_+ = 2.5 \text{ V})$



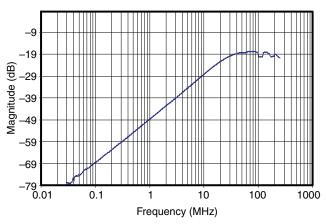
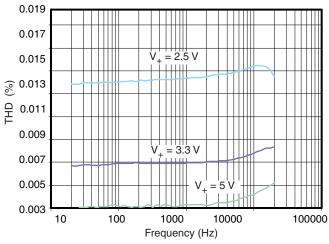


Figure 10. OFF Isolation vs Frequency

Figure 11. Crosstalk ($V_+ = 3.3 \text{ V}$)



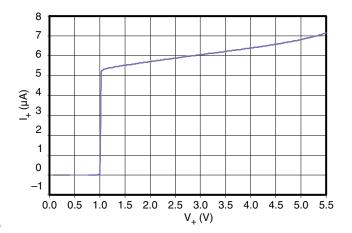


Figure 12. Total Harmonic Distortion vs Frequency

Figure 13. Power-Supply Current vs V+



TYPICAL PERFORMANCE (continued)

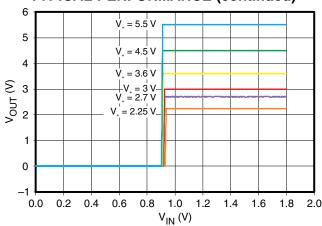


Figure 14. Control Input Thresholds



PARAMETER MEASUREMENT INFORMATION

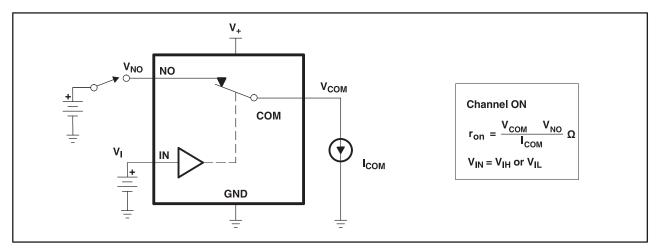


Figure 15. ON-state Resistance (r_{ON})

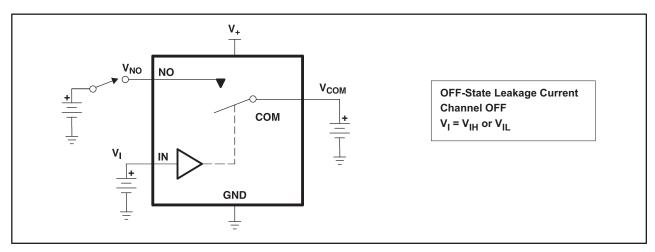


Figure 16. OFF-State Leakage Current (I_{COM(OFF)}, I_{NC(OFF)}, I_{COM(PWROFF)}, I_{NC(PWROFF)})



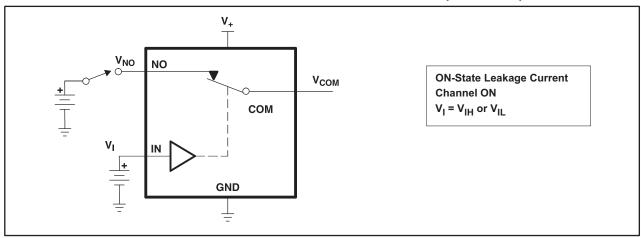


Figure 17. ON-State Leakage Current (I_{COM(ON)}, I_{NC(ON)})

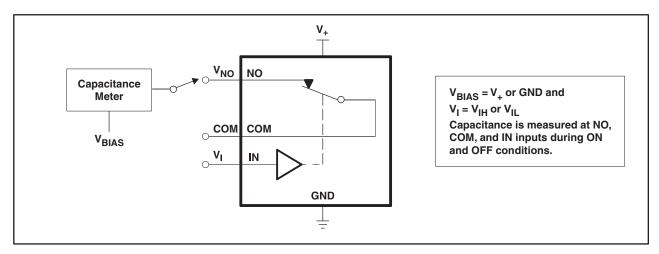


Figure 18. Capacitance (C_I, C_{COM(OFF)}, C_{COM(ON)}, C_{NC(OFF)}, C_{NC(ON)})

- A. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_r < 5 \text{ ns}$, $t_f < 5 \text{ ns}$.
- B. C_L includes probe and jig capacitance.



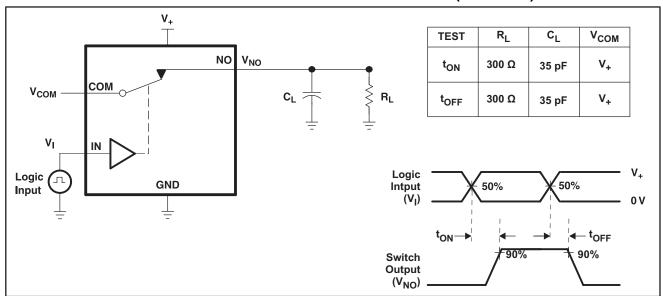


Figure 19. Turn-On (t_{ON}) and Turn-Off Time (t_{OFF})

- A. C_L includes probe and jig capacitance.
- B. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_0 = 50 \Omega$, $t_r < 5 \text{ ns}$, $t_f < 5 \text{ ns}$.

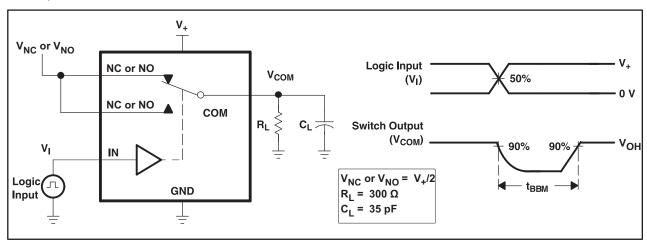


Figure 20. Break-Before-Make Time (t_{BBM})



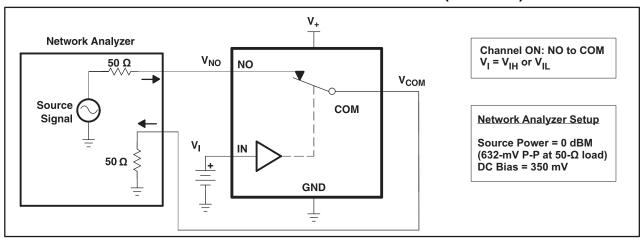


Figure 21. Bandwidth (BW)

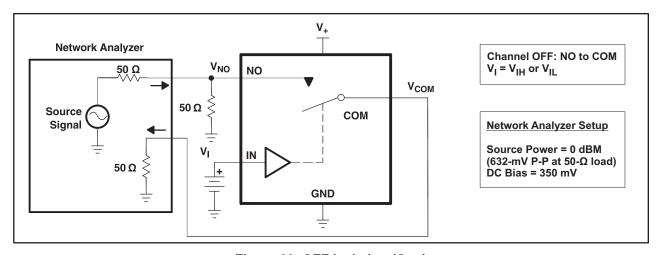


Figure 22. OFF Isolation (O_{ISO})

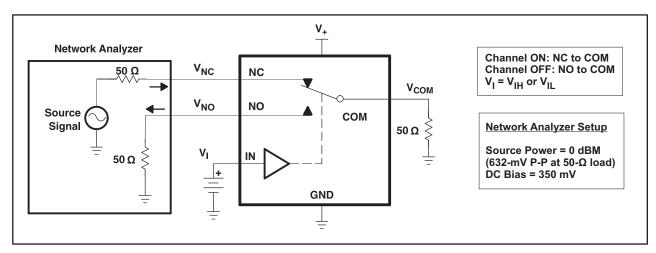


Figure 23. Crosstalk (X_{TALK})

- A. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_r < 5 \text{ ns}$, $t_f < 5 \text{ ns}$.
- B. C_L includes probe and jig capacitance.



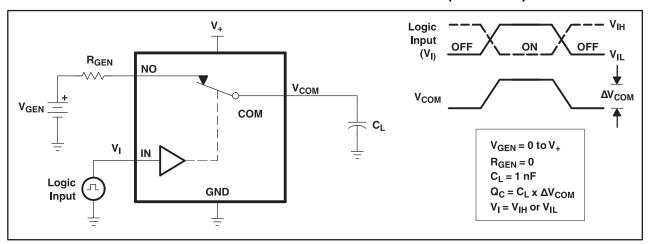


Figure 24. Charge Injection (Q_C)

A. C_L includes probe and jig capacitance.

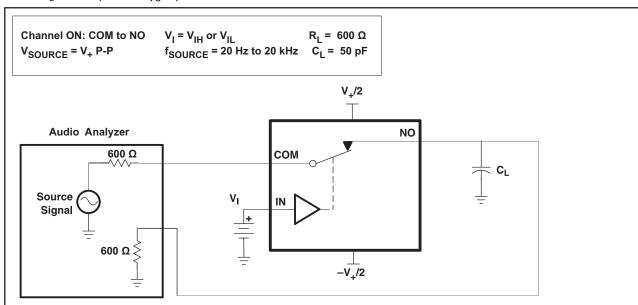


Figure 25. Total Harmonic Distortion (THD)



REVISION HISTORY

CI	Changes from Revision A (August 2009) to Revision B						
•	Removed QFN reference from product description.	1					
•	Changed Analog signal range MIN value from V ₊ – 0.5 to V ₊ – 5.5	7					

Product Folder Links: TS5A22366



PACKAGE OPTION ADDENDUM

10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
TS5A22366YFCR	ACTIVE	DSBGA	YFC	12	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(3A2, 3AN)	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 23-Mar-2024

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS5A22366YFCR	DSBGA	YFC	12	3000	178.0	9.2	1.29	1.69	0.73	4.0	8.0	Q1

PACKAGE MATERIALS INFORMATION

www.ti.com 23-Mar-2024

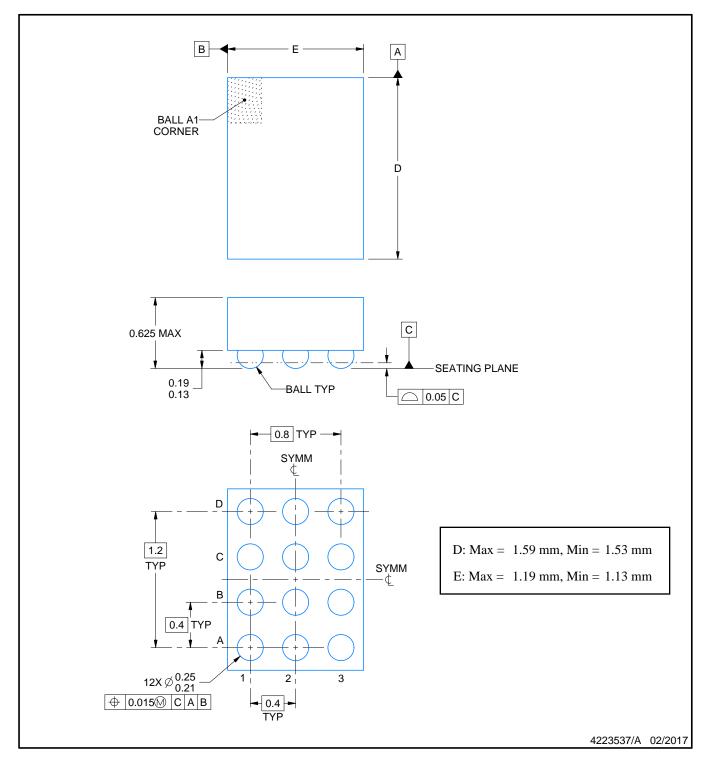


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS5A22366YFCR	DSBGA	YFC	12	3000	220.0	220.0	35.0



DIE SIZE BALL GRID ARRAY

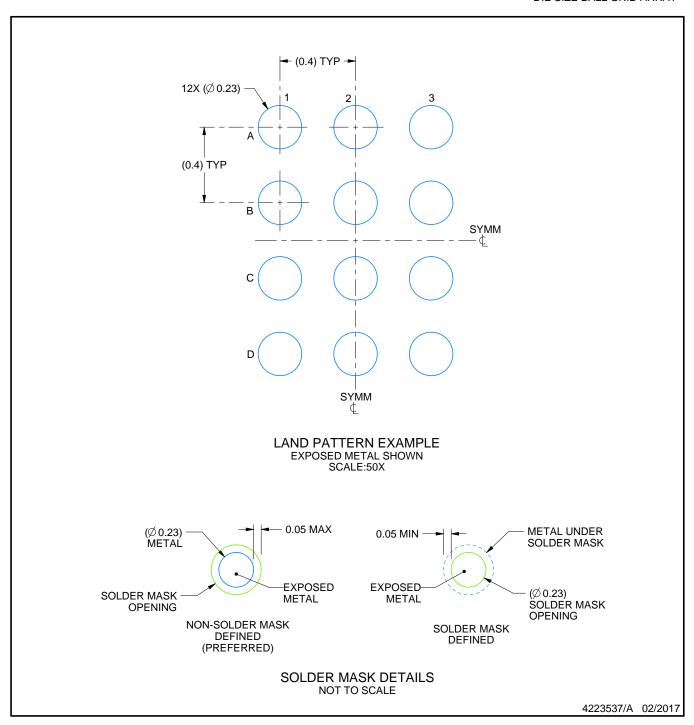


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY

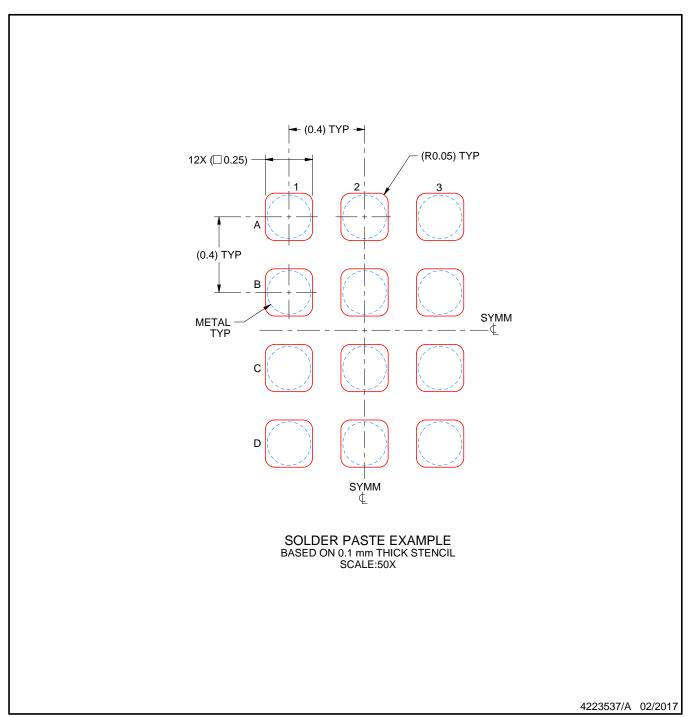


NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2024, Texas Instruments Incorporated